

PERFORMANCE CURVES

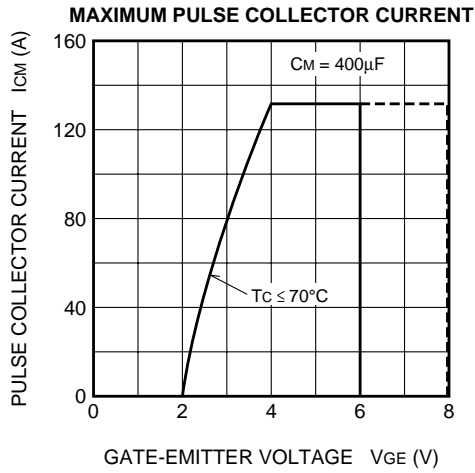
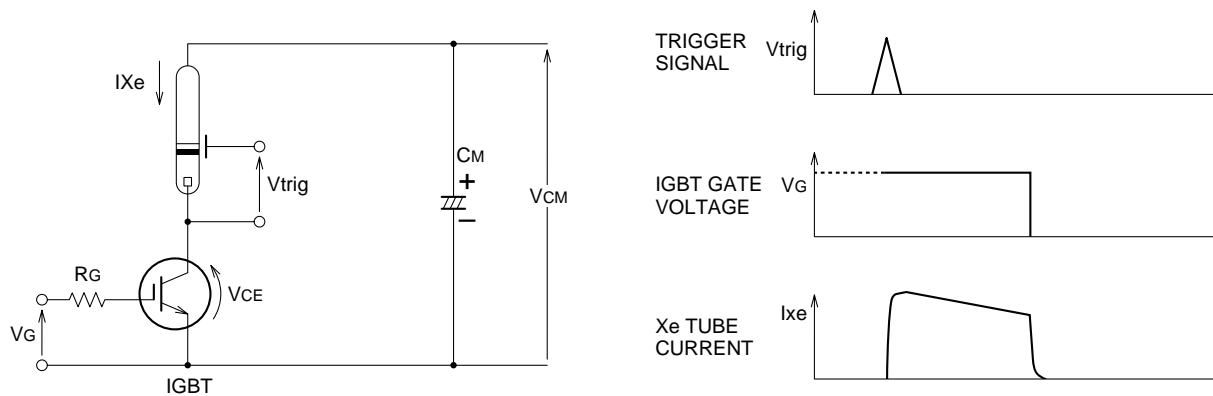


Figure 1

APPLICATION EXAMPLE



RECOMMEND CONDITION	MAXIMUM CONDITION
$V_{CM} = 330V$	350V
$I_{CP} = 120A$	130A
$C_M = 300\mu F$	400 μF
$V_{GE} = 5V$	

- Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And reverse gate current during turn-off must be kept less than 0.1A. (In general, it is satisfied if $R_G \geq 30\Omega$)
- Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully not to suffer from electrostatic charge.
- Notice 3. The operation life should be endured 5,000 shots under the charge current ($I_{xe} \leq 130A$: full luminescence condition) of main condenser ($C_M=400\mu F$). Repetition period under full luminescence condition is over 3 seconds.
- Notice 4. Total operation hours must be applied within 5,000 hours.